



10A CELL SERIES

硅整流器 Silicon Rectifier

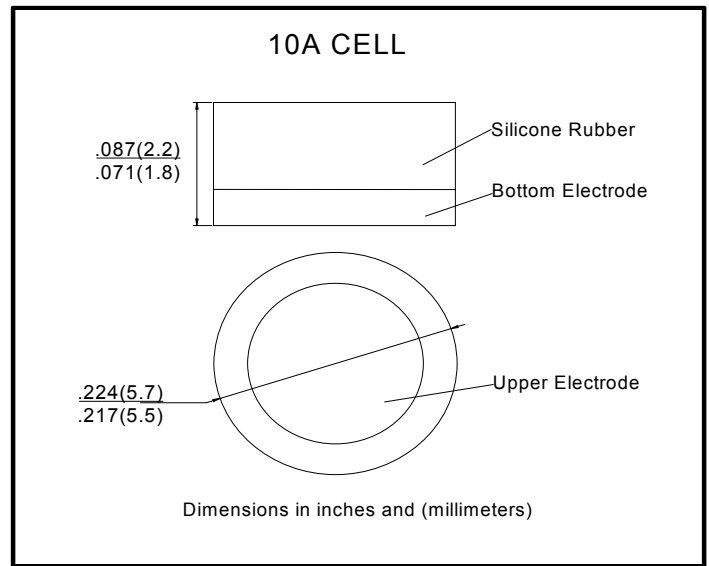
■特征 Features

- I_o 10A
- V_{RRM} 100V~1000V
- 电极表面高可焊性
Solderable electrode surface
- 耐正向浪涌电流能力高
High surge forward current capability

■用途 Applications

- 作一般单相整流用
General purpose 1 phase rectifier applications

■外形尺寸和印记 Outline Dimensions and Mark



■极限值（绝对最大额定值）

Limiting Values (Absolute Maximum Rating)

参数名称 Item	符号 Symbol	单位 Unit	条件 Conditions	10A					
				100V	200V	400V	600V	800V	1000V
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		100	200	400	600	800	1000
平均整流输出电流 Average Rectified Output Current	I_o	A	60Hz 正弦波, 电阻负载, $T_a=50^\circ\text{C}$ 60Hz sine wave, R- load, $T_a=50^\circ\text{C}$	10					
正向（不重复）浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz正弦波, 一个周期, $T_a=25^\circ\text{C}$ 60Hz sine wave, 1 cycle, $T_a=25^\circ\text{C}$	300					
正向浪涌电流的平方对电流浪涌持续时间的积分值 Current Squared Time	$I^2 t$	$A^2 s$	1ms ≤ t < 8.3ms $T_j=25^\circ\text{C}$, 单个二极管 1ms ≤ t < 8.3ms $T_j=25^\circ\text{C}$, Rating of per diode	375					
存储温度 Storage Temperature	T_{STG}	$^\circ\text{C}$		-55 ~ +150					
结温 Junction Temperature	T_j	$^\circ\text{C}$		-55 ~ +125					

■电特性（ $T_a=25^\circ\text{C}$ 除非另有规定）

Electrical Characteristics ($T_a=25^\circ\text{C}$ Unless otherwise specified)

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Test Condition	最大值 Max
正向峰值电压 Peak Forward Voltage	V_{FM}	V	$I_{FM}=10\text{A}$, 脉冲测试, 单个二极管的额定值 $I_{FM}=10\text{A}$, Pulse measurement, Rating of per diode	1.1
反向峰值电流 Peak Reverse Current	I_{RRM1}	μA	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$
	I_{RRM2}			$T_a=125^\circ\text{C}$
热阻 Thermal Resistance	$R_{\theta J-A}$	$^\circ\text{C/W}$	结和环境之间 Between junction and ambient	7.5



■ 特性曲线 (典型) Characteristics(Typical)

图1: I_o - T_a 曲线
FIG1: I_o - T_a Curve

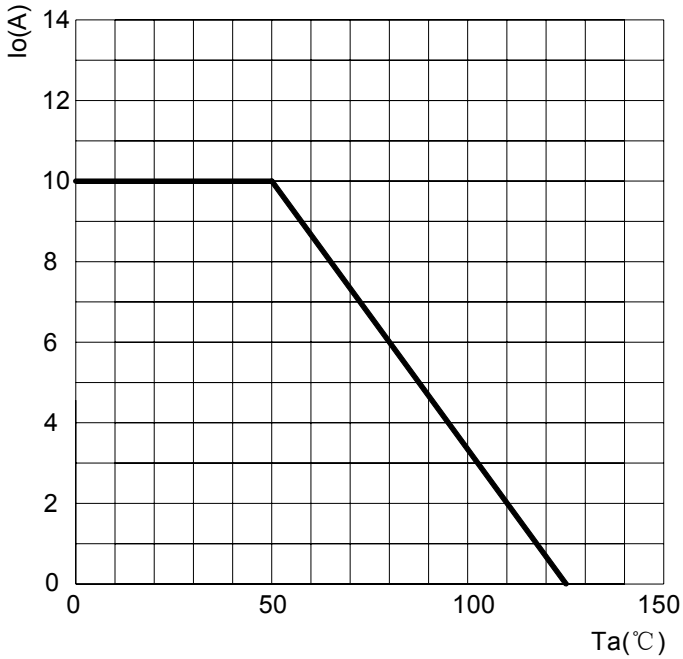


图2: 耐正向浪涌电流曲线
FIG2: Surge Forward Current Capadility

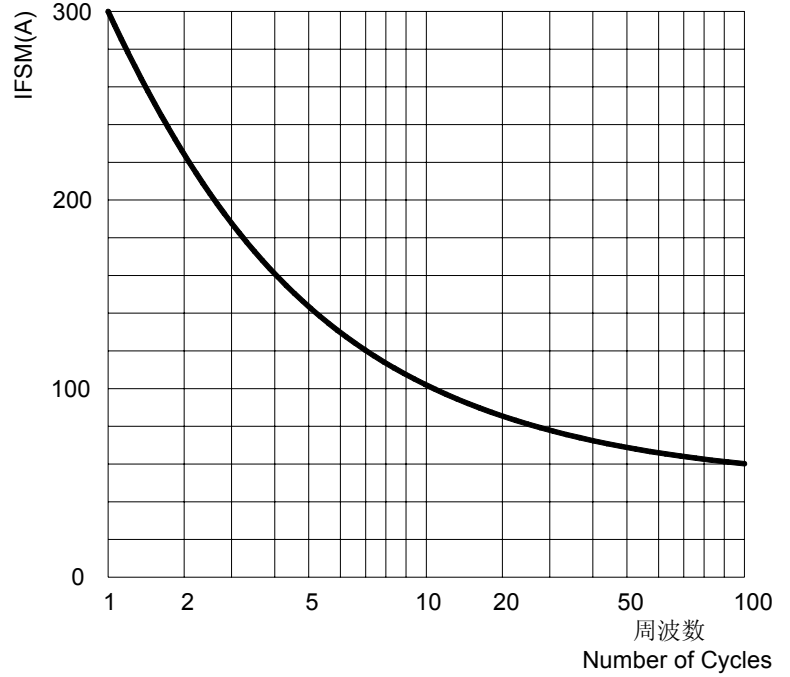


图3: 正向电压曲线
FIG3: Instantaneous Forward Voltage

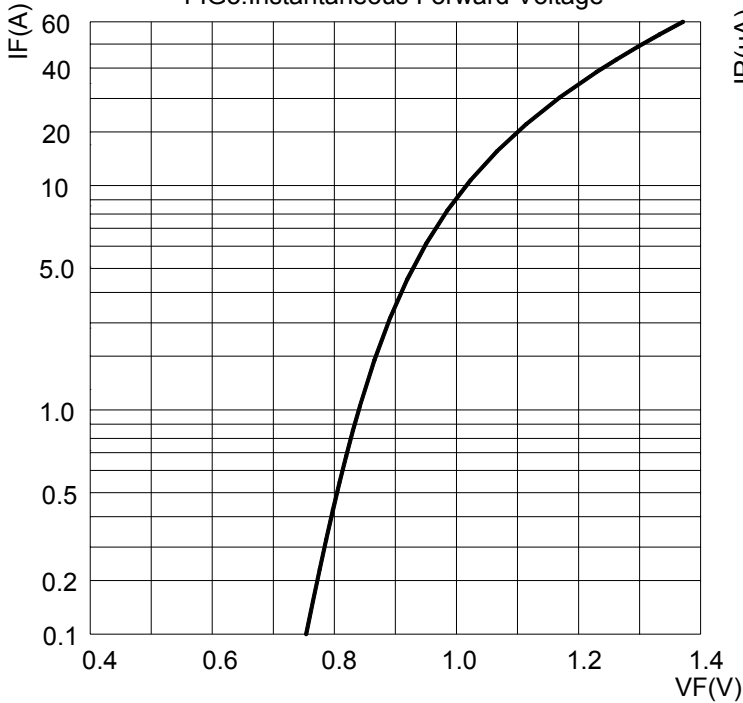


图4: 反向电流曲线
FIG4: Typical Reverse Characteristics

